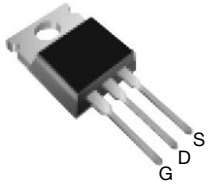
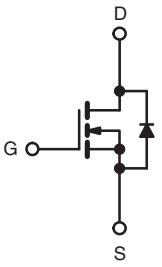
# D Series Power MOSFET

| PRODUCT SUMMARY | | |
|---|---|---|
| $V_{DS}$ (V) at $T_J$ max. | 550 | |
| $R_{DS(on)}$ max. at 25 °C (Ω) | $V_{GS}$ = 10 V | 0.4 |
| $Q_g$ max. (nC) | 58 | |
| $Q_{gs}$ (nC) | 8 | |
| $Q_{gd}$ (nC) | 14 | |
| Configuration | Single | |

TO-220AB




N-Channel MOSFET

## FEATURES

- Optimal Design
  - Low Area specific On-Resistance
  - Low Input Capacitance ($C_{iss}$)
  - Reduced Capacitive Switching Losses
  - High Body Diode Ruggedness
  - Avalanche Energy Rated ($U_{IS}$)
- Optimal Efficiency and Operation
  - Low Cost
  - Simple Gate Drive Circuitry
  - Low Figure-Of-Merit (FOM): $R_{on}$ x $Q_g$
  - Fast Switching
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

RoHS* COMPLIANT

HALOGEN FREE Available

**Note**

* Lead (Pb)-containing terminations are not RoHS-compliant. Exemptions may apply.

## APPLICATIONS

- Consumer Electronics
  - Displays (LCD or Plasma TV
- Server and Telecom Power Supplies
  - SMPS
- Industrial
  - Welding, Induction Heating, Motor Drives
- Battery Chargers

| ORDERING INFORMATION | |
|---|---|
| Package | TO-220AB |
| Lead (Pb)-free | SiHP14N50D-E3 |
| Lead (Pb)-free and Halogen-free | SiHP14N50D-GE3 |

**ABSOLUTE MAXIMUM RATINGS** ($T_C$ = 25 °C, unless otherwise noted)

| PARAMETER | | | SYMBOL | LIMIT | UNIT |
|---|---|---|---|---|---|
| Drain-Source Voltage | | | $V_{DS}$ | 500 | V |
| Gate-Source Voltage | | | $V_{GS}$ | ± 30 | |
| Gate-Source Voltage AC (f > 1 Hz) | | | | 30 | |
| Continuous Drain Current ($T_J$ = 150 °C) | $V_{GS}$ at 10 V | $T_C$ = 25 °C | $I_D$ | 14 | A |
| | | $T_C$ = 100 °C | | 9 | |
| Pulsed Drain Current[a] | | | $I_{DM}$ | 38 | |
| Linear Derating Factor | | | | 1.6 | W/°C |
| Single Pulse Avalanche Energy[b] | | | $E_{AS}$ | 56 | mJ |
| Maximum Power Dissipation | | | $P_D$ | 208 | W |
| Operating Junction and Storage Temperature Range | | | $T_J$, $T_{stg}$ | - 55 to + 150 | °C |
| Drain-Source Voltage Slope | $T_J$ = 125 °C | | dV/dt | 24 | V/ns |
| Reverse Diode dV/dt[d] | | | | 0.4 | |
| Soldering Recommendations (Peak Temperature) | for 10 s | | | 300[c] | °C |

**Notes**

a. Repetitive rating; pulse width limited by maximum junction temperature.
b. $V_{DD}$ = 50 V, starting $T_J$ = 25 °C, L = 2.3 mH, $R_g$ = 25 Ω, $I_{AS}$ = 7 A.
c. 1.6 mm from case.
d. $I_{SD} \leq I_D$, starting $T_J$ = 25 °C.

| THERMAL RESISTANCE RATINGS | | | | |
|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TYP.** | **MAX.** | **UNIT** |
| Maximum Junction-to-Ambient | $R_{thJA}$ | - | 62 | °C/W |
| Maximum Junction-to-Case (Drain) | $R_{thJC}$ | - | 0.6 | |

**SPECIFICATIONS** ($T_J$ = 25 °C, unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---|---|---|---|---|---|---|
| **Static** | | | | | | |
| Drain-Source Breakdown Voltage | $V_{DS}$ | $V_{GS}$ = 0 V, $I_D$ = 250 µA | 500 | - | - | V |
| $V_{DS}$ Temperature Coefficient | $\Delta V_{DS}/T_J$ | Reference to 25 °C, $I_D$ = 250 µA | - | 0.58 | - | V/°C |
| Gate Threshold Voltage (N) | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 µA | 3.0 | - | 5.0 | V |
| Gate-Source Leakage | $I_{GSS}$ | $V_{GS}$ = ± 30 V | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = 500 V, $V_{GS}$ = 0 V | - | - | 1 | µA |
| | | $V_{DS}$ = 400 V, $V_{GS}$ = 0 V, $T_J$ = 125 °C | - | - | 10 | |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS}$ = 10 V, $I_D$ = 7 A | - | 0.320 | 0.40 | Ω |
| Forward Transconductance[a] | $g_{fs}$ | $V_{DS}$ = 50 V, $I_D$ = 7 A | - | 5.2 | - | S |
| **Dynamic** | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{GS}$ = 0 V, $V_{DS}$ = 100 V, f = 1 MHz | - | 1144 | - | pF |
| Output Capacitance | $C_{oss}$ | | - | 100 | - | |
| Reverse Transfer Capacitance | $C_{rss}$ | | - | 12 | - | |
| Effective Output Capacitance, Energy Related[a] | $C_{o(er)}$ | $V_{GS}$ = 0 V, $V_{DS}$ = 0 V to 480 V | - | 87 | - | |
| Effective Output Capacitance, Time Related[b] | $C_{o(tr)}$ | | - | 125 | - | |
| Total Gate Charge | $Q_g$ | $V_{GS}$ = 10 V; $I_D$ = 7 A, $V_{DS}$ = 400 V | - | 29 | 58 | nC |
| Gate-Source Charge | $Q_{gs}$ | | - | 8 | - | |
| Gate-Drain Charge | $Q_{gd}$ | | - | 14 | - | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD}$ = 400 V, $I_D$ = 7 A, $V_{GS}$ = 10 V, $R_g$ = 9.1 Ω | - | 16 | 32 | ns |
| Rise Time | $t_r$ | | - | 27 | 54 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 29 | 58 | |
| Fall Time | $t_f$ | | - | 26 | 52 | |
| Gate Input Resistance | $R_g$ | f = 1 MHz, open drain | - | 1.7 | - | Ω |
| **Drain-Source Body Diode Characteristics** | | | | | | |
| Continuous Source-Drain Diode Current | $I_S$ | MOSFET symbol showing the integral reverse p - n junction diode  | - | - | 14 | A |
| Pulsed Diode Forward Current | $I_{SM}$ | | - | - | 56 | |
| Diode Forward Voltage | $V_{SD}$ | $T_J$ = 25 °C, $I_S$ = 7 A, $V_{GS}$ = 0 V | - | - | 1.2 | V |
| Reverse Recovery Time | $t_{rr}$ | $T_J$ = 25 °C, $I_F$ = $I_S$ = 7 A, dI/dt = 100 A/µs, $V_R$ = 20 V | - | 319 | - | ns |
| Reverse Recovery Charge | $Q_{rr}$ | | - | 3.0 | - | µC |
| Reverse Recovery Current | $I_{RRM}$ | | - | 18 | - | A |

**Notes**

a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as $C_{oss}$ while $V_{DS}$ is rising from 0 % to 80 % $V_{DSS}$.

b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as $C_{oss}$ while $V_{DS}$ is rising from 0 % to 80 % $V_{DSS}$.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

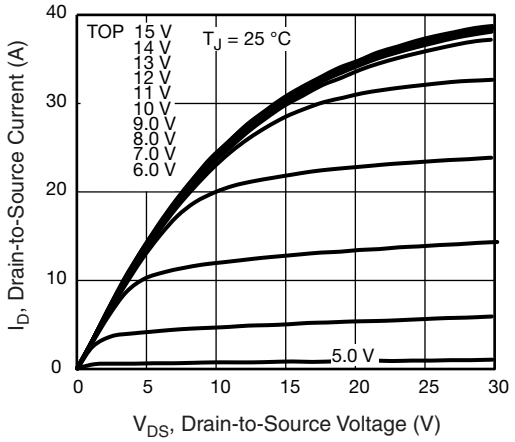



**Fig. 1 - Typical Output Characteristics**

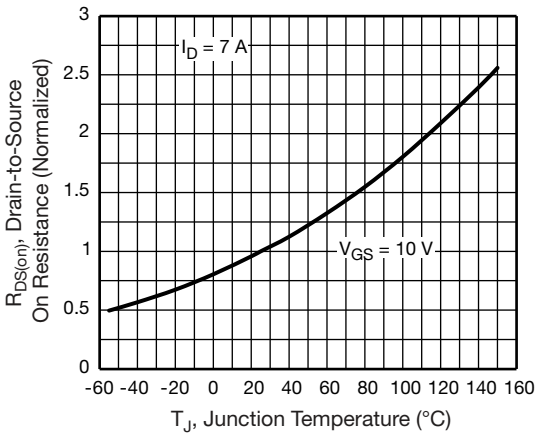



**Fig. 4 - Normalized On-Resistance vs. Temperature**

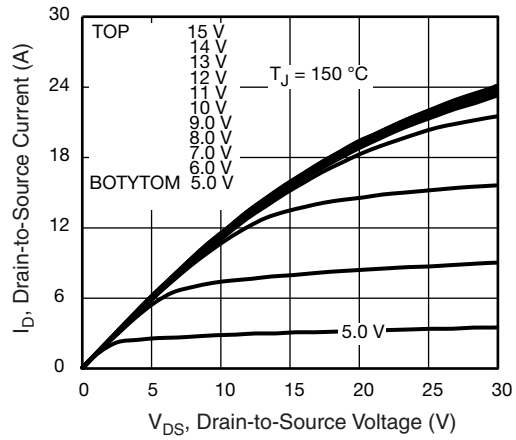



**Fig. 2 - Typical Output Characteristics**

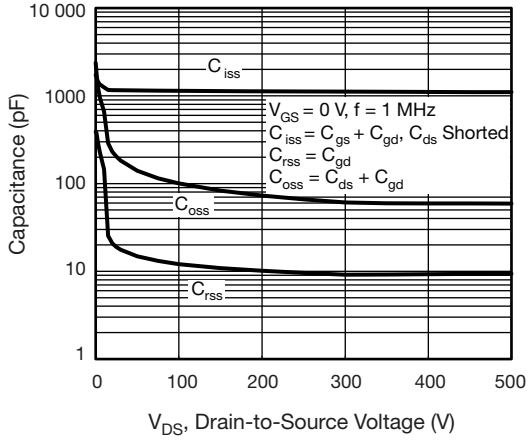



**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

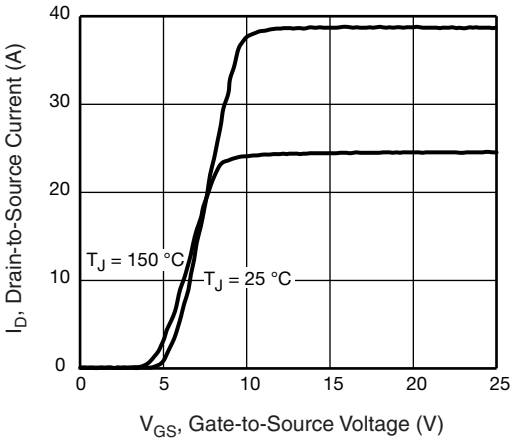



**Fig. 3 - Typical Transfer Characteristics**

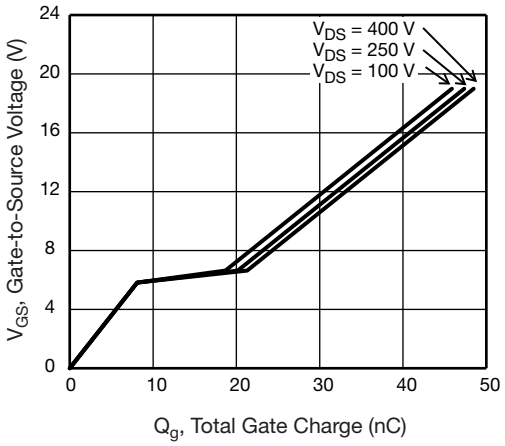



**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**

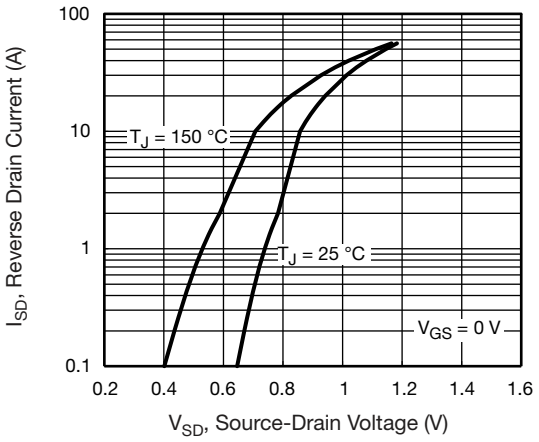



**Fig. 7 - Typical Source-Drain Diode Forward Voltage**

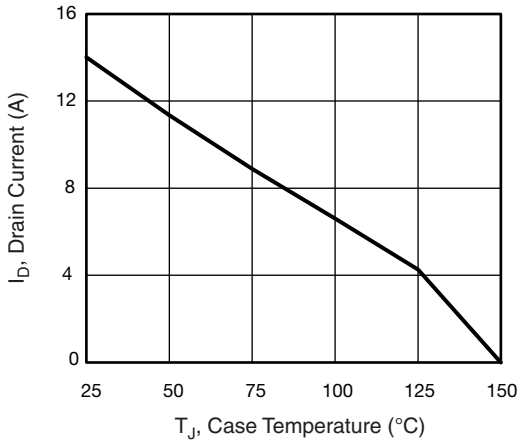



**Fig. 9 - Maximum Drain Current vs. Case Temperature**

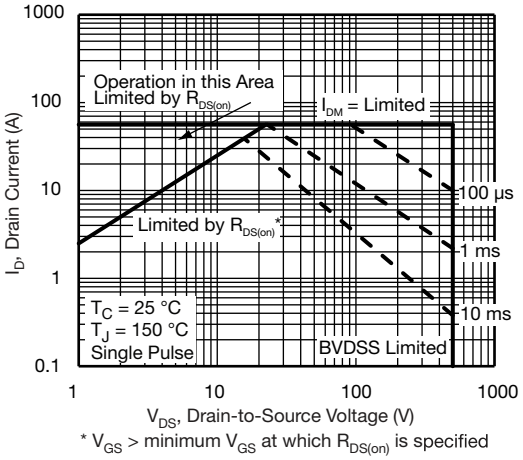



**Fig. 8 - Maximum Safe Operating Area**

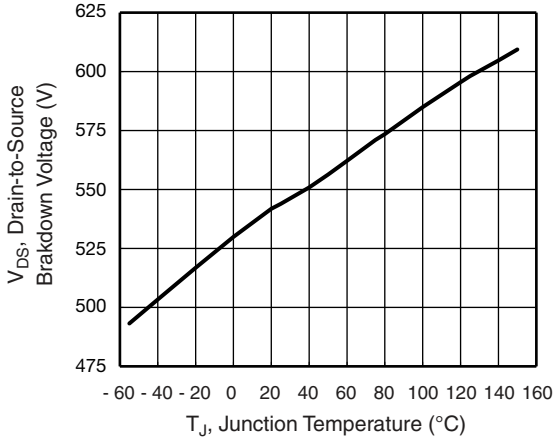



**Fig. 10 - Temperature vs. Drain-to-Source Voltage**

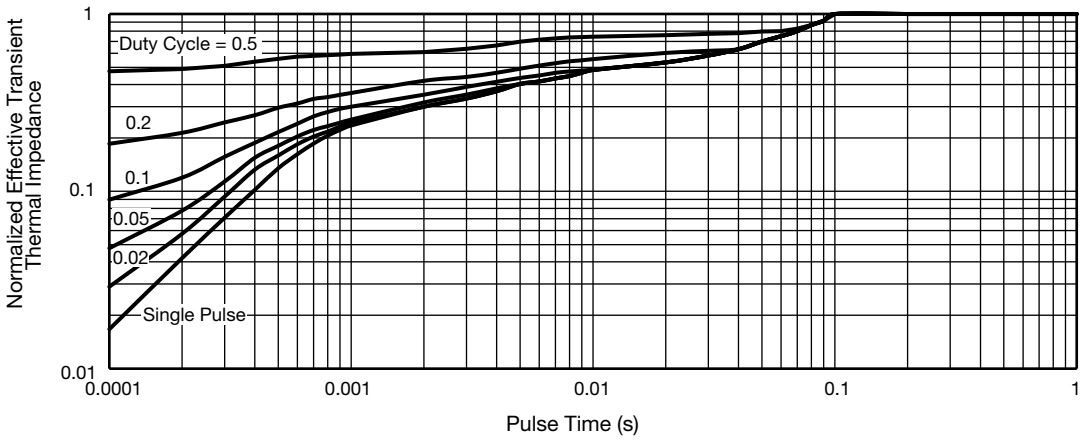



**Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case**

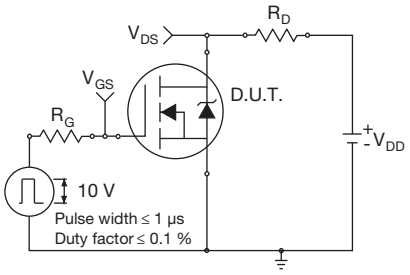



**Fig. 12 - Switching Time Test Circuit**

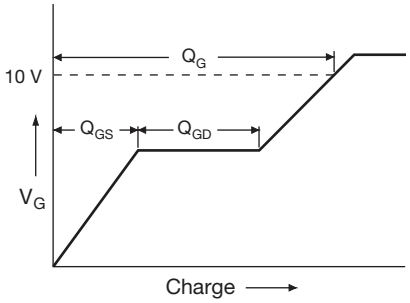



**Fig. 16 - Basic Gate Charge Waveform**

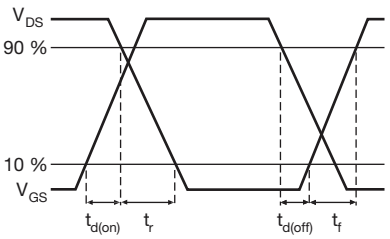



**Fig. 13 - Switching Time Waveforms**

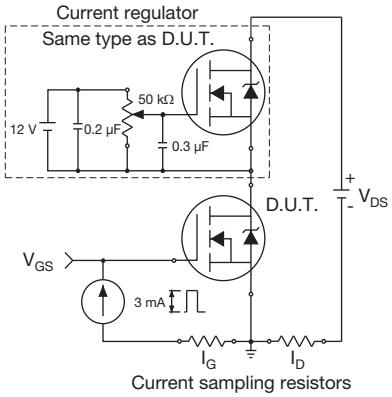



**Fig. 17 - Gate Charge Test Circuit**

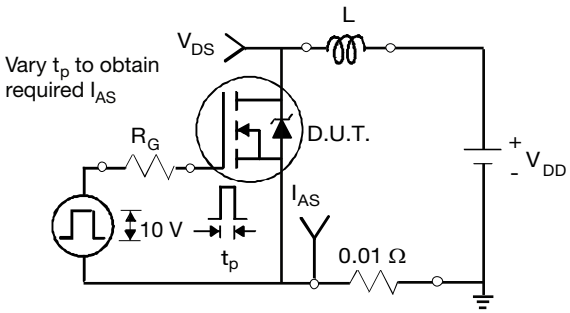



**Fig. 14 - Unclamped Inductive Test Circuit**

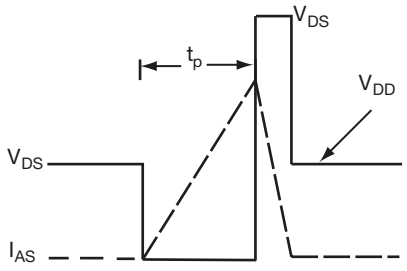
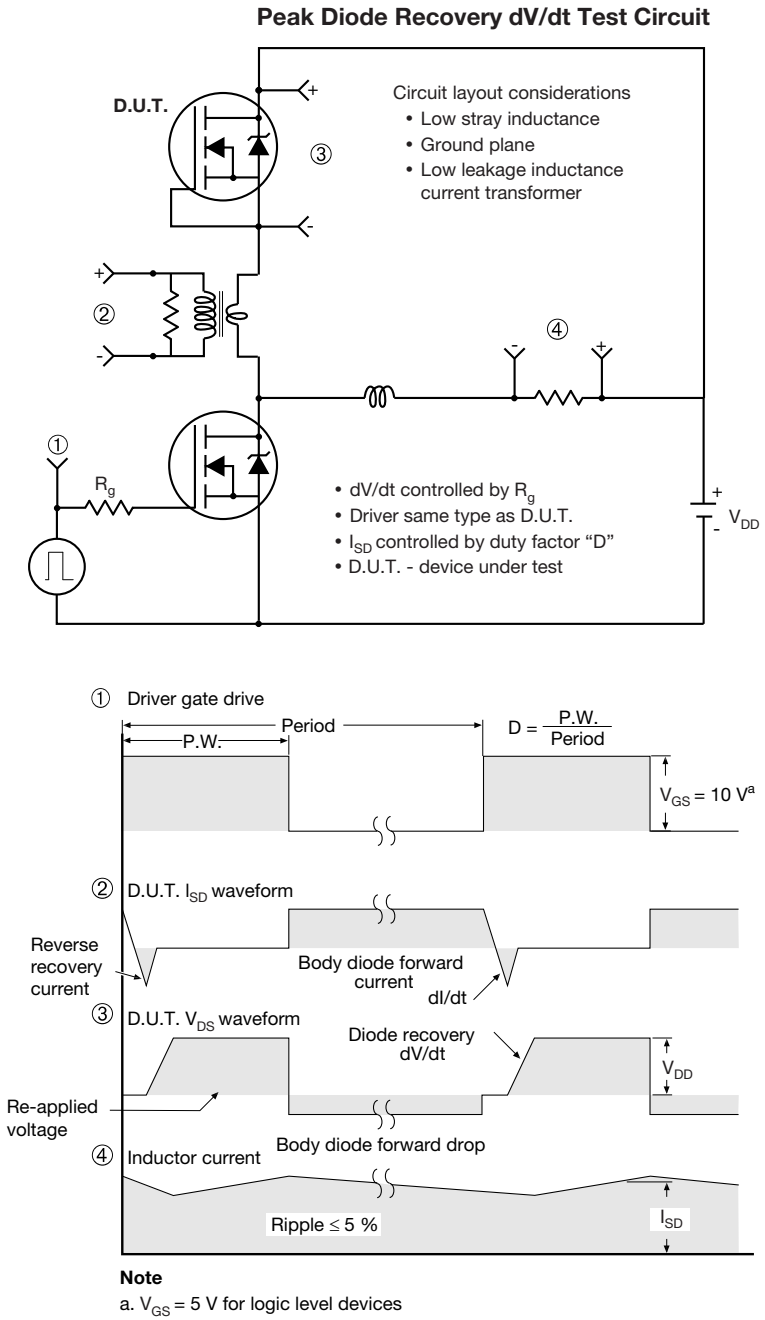



**Fig. 15 - Unclamped Inductive Waveforms**



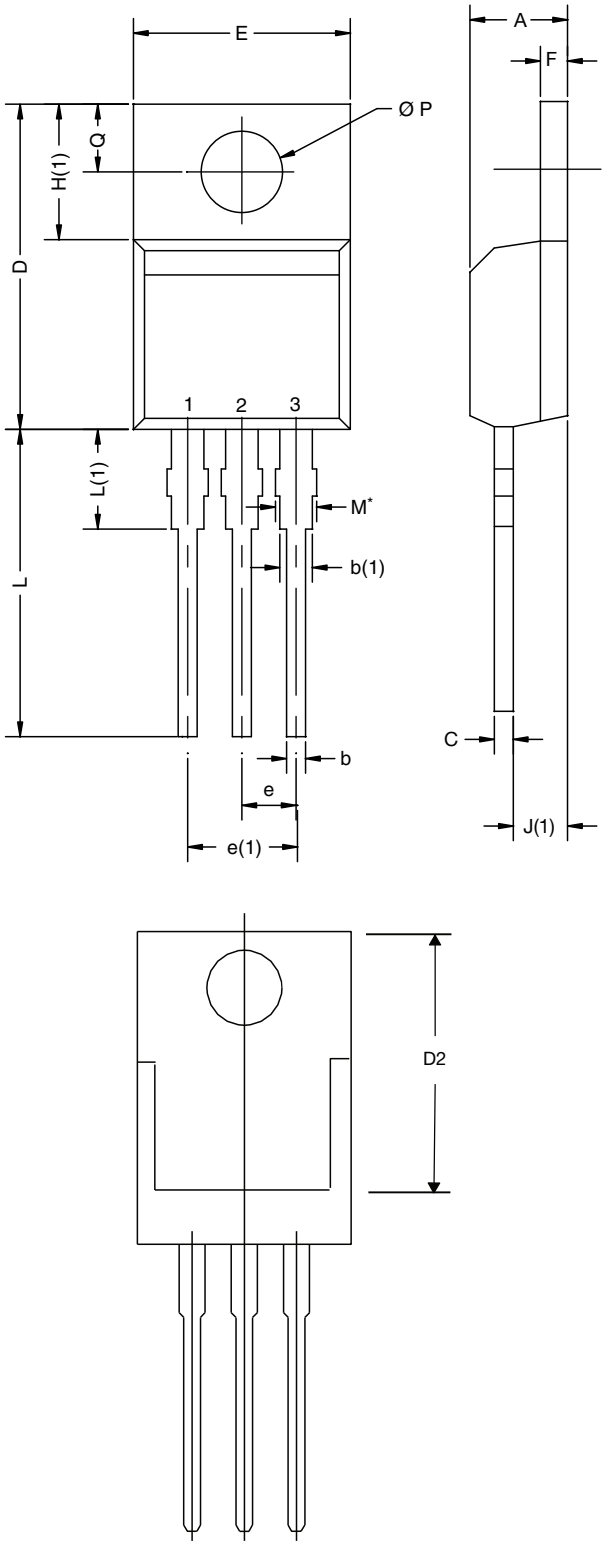

**Note**

a. $V_{GS}$ = 5 V for logic level devices

**Fig. 18 - For N-Channel**

*Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91512.*

# TO-220AB




| DIM. | MILLIMETERS | | INCHES | |
|---|---|---|---|---|
| | MIN. | MAX. | MIN. | MAX. |
| A | 4.25 | 4.65 | 0.167 | 0.183 |
| b | 0.69 | 1.01 | 0.027 | 0.040 |
| b(1) | 1.20 | 1.73 | 0.047 | 0.068 |
| c | 0.36 | 0.61 | 0.014 | 0.024 |
| D | 14.85 | 15.49 | 0.585 | 0.610 |
| D2 | 12.19 | 12.70 | 0.480 | 0.500 |
| E | 10.04 | 10.51 | 0.395 | 0.414 |
| e | 2.41 | 2.67 | 0.095 | 0.105 |
| e(1) | 4.88 | 5.28 | 0.192 | 0.208 |
| F | 1.14 | 1.40 | 0.045 | 0.055 |
| H(1) | 6.09 | 6.48 | 0.240 | 0.255 |
| J(1) | 2.41 | 2.92 | 0.095 | 0.115 |
| L | 13.35 | 14.02 | 0.526 | 0.552 |
| L(1) | 3.32 | 3.82 | 0.131 | 0.150 |
| Ø P | 3.54 | 3.94 | 0.139 | 0.155 |
| Q | 2.60 | 3.00 | 0.102 | 0.118 |
| ECN: T14-0413-Rev. P, 16-Jun-14<br>DWG: 5471 | | | | |

**Note**

* M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM

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